

MPSA92 / 93

PNP Silicon Expitaxial Planar Transistor

for high voltage switching and amplifier applications.

As complementary type the NPN transistor
MPSA42 and MPSA 43 are recommended.

On special request, these transistors can be
manufactured in different pin configurations.



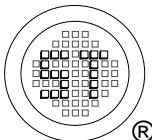
1. Emitter 2. Base 3. Collector
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage MPSA92 MPSA93	$-V_{CBO}$	300 200	V
Collector Emitter Voltage MPSA92 MPSA93	$-V_{CEO}$	300 200	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	500	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-I_C = 1 \text{ mA}$, $-V_{CE} = 10 \text{ V}$ at $-I_C = 10 \text{ mA}$, $-V_{CE} = 10 \text{ V}$ at $-I_C = 30 \text{ mA}$, $-V_{CE} = 10 \text{ V}$	h_{FE} h_{FE} h_{FE}	25 40 25	- - -	- - -
Collector Base Cutoff Current at $-V_{CB} = 200 \text{ V}$ at $-V_{CB} = 160 \text{ V}$	$-I_{CBO}$ $-I_{CBO}$	- -	0.25 0.25	μA μA
Emitter Base Cutoff Current at $-V_{EB} = 3 \text{ V}$	$-I_{EBO}$	-	0.1	μA
Collector Base Breakdown Voltage at $-I_C = 100 \mu\text{A}$	$-V_{(BR)CBO}$ $-V_{(BR)CBO}$	300 200	- -	V V
Collector Emitter Breakdown Voltage at $-I_C = 1 \text{ mA}$	$-V_{(BR)CEO}$ $-V_{(BR)CEO}$	300 200	- -	V V
Emitter Base Breakdown Voltage at $-I_E = 100 \mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 20 \text{ mA}$, $-I_B = 2 \text{ mA}$	$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C = 20 \text{ mA}$, $-I_B = 2 \text{ mA}$	$-V_{BE(sat)}$	-	0.9	V
Gain Bandwidth Product at $-I_C = 10 \text{ mA}$, $-V_{CE} = 20 \text{ V}$, $f = 100 \text{ MHz}$	f_T	50	-	MHz
Collector Output Capacitance at $-V_{CB} = 20 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob} C_{ob}	- -	6 8	pF pF



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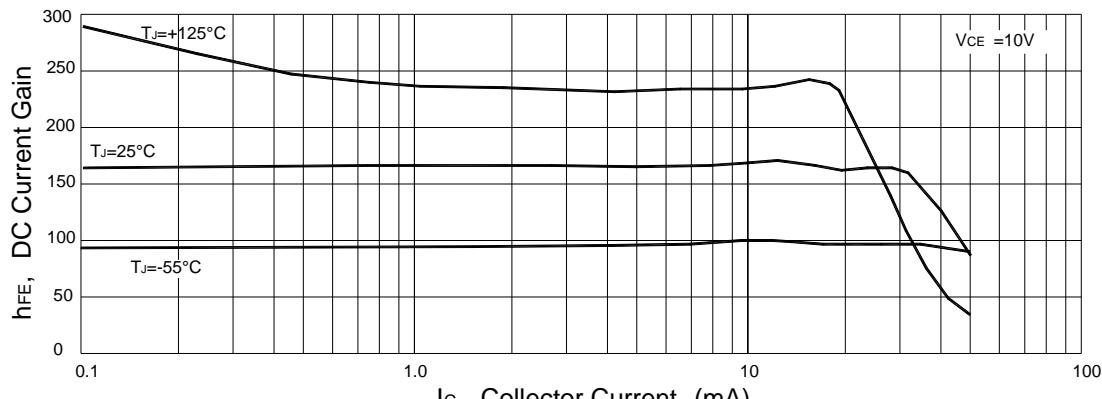


Figure 1. DC Current Gain

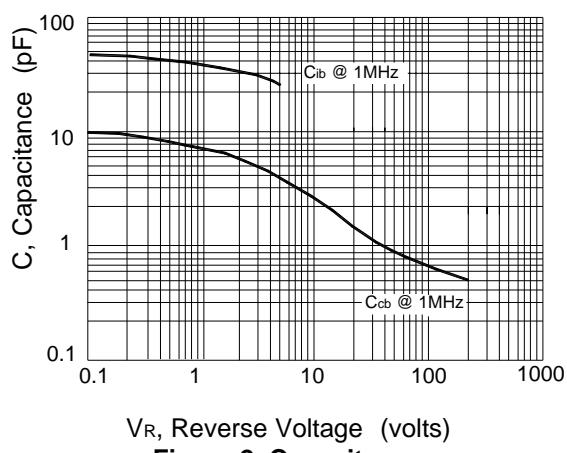


Figure 2. Capacitance

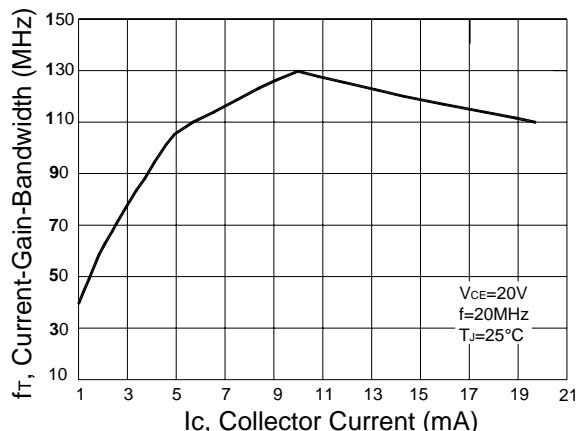
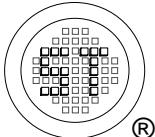


Figure 3. Current-Gain-Bandwidth



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